

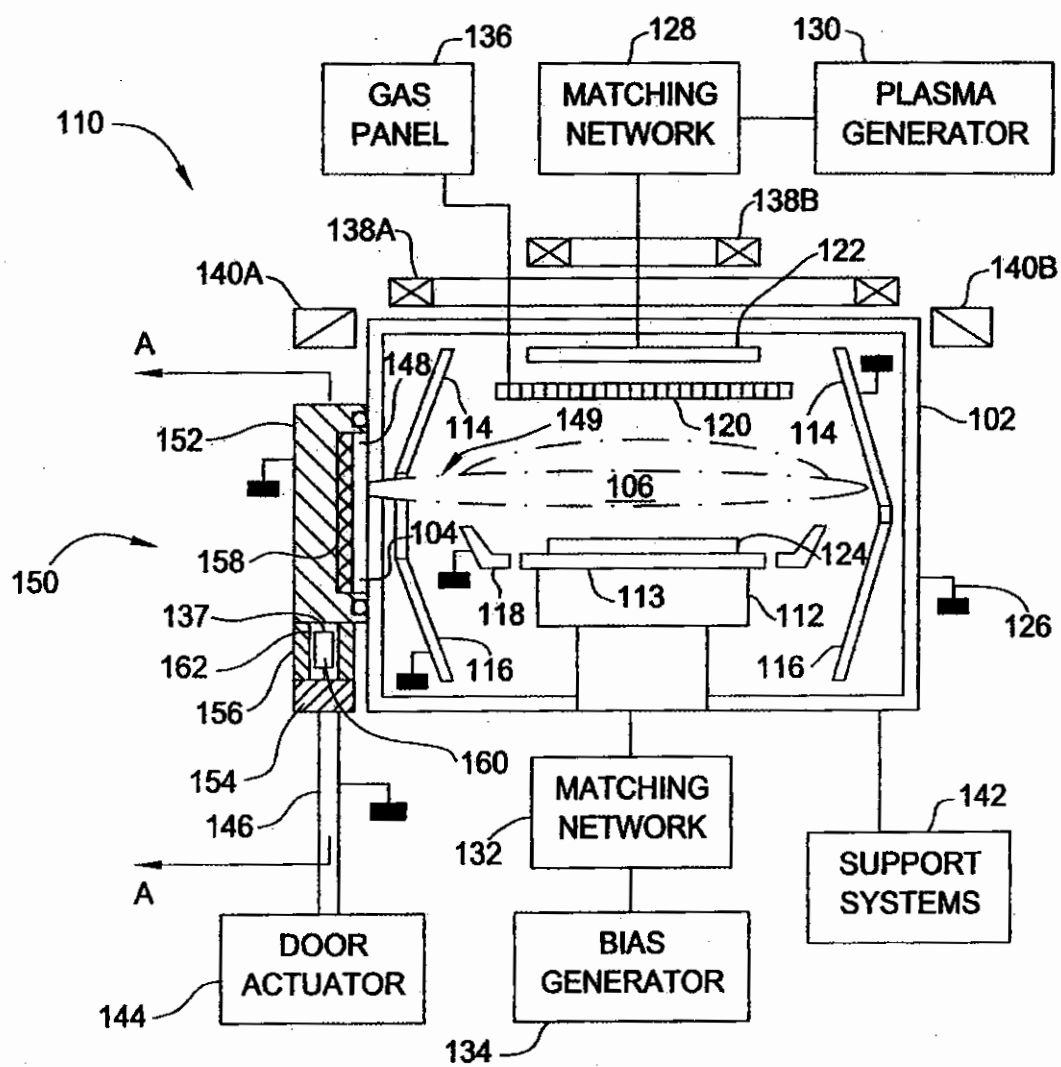


FIG. 1

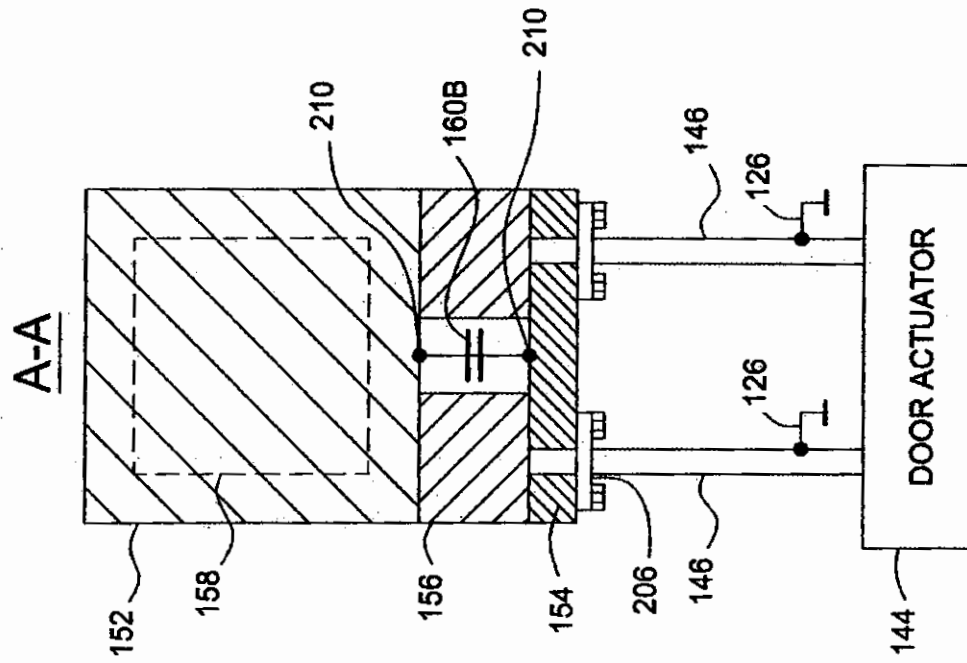


FIG. 2B

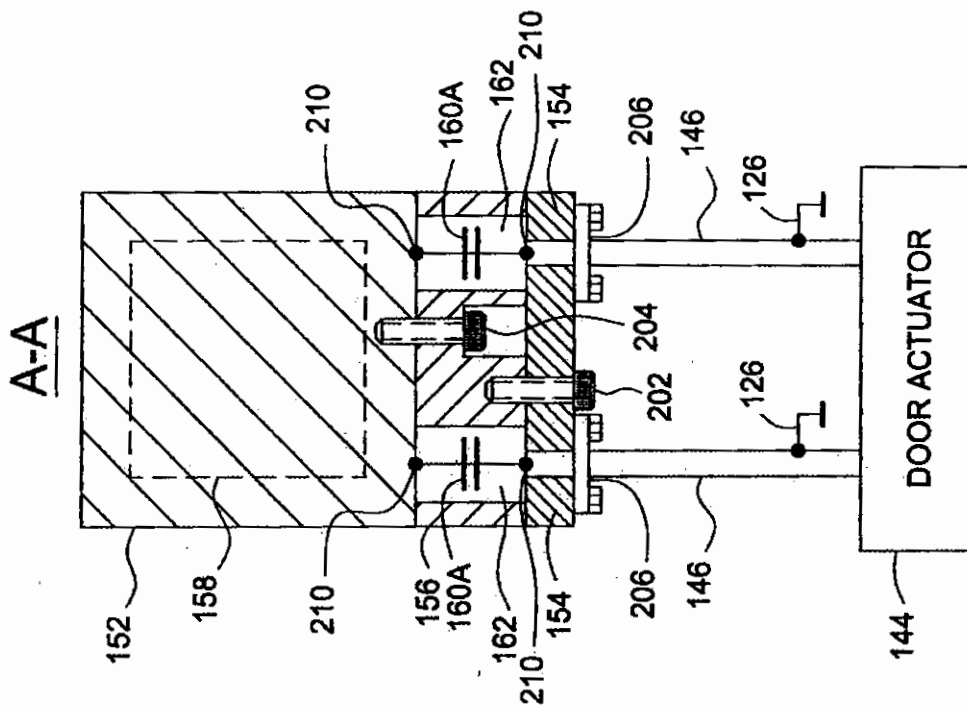


FIG. 2A

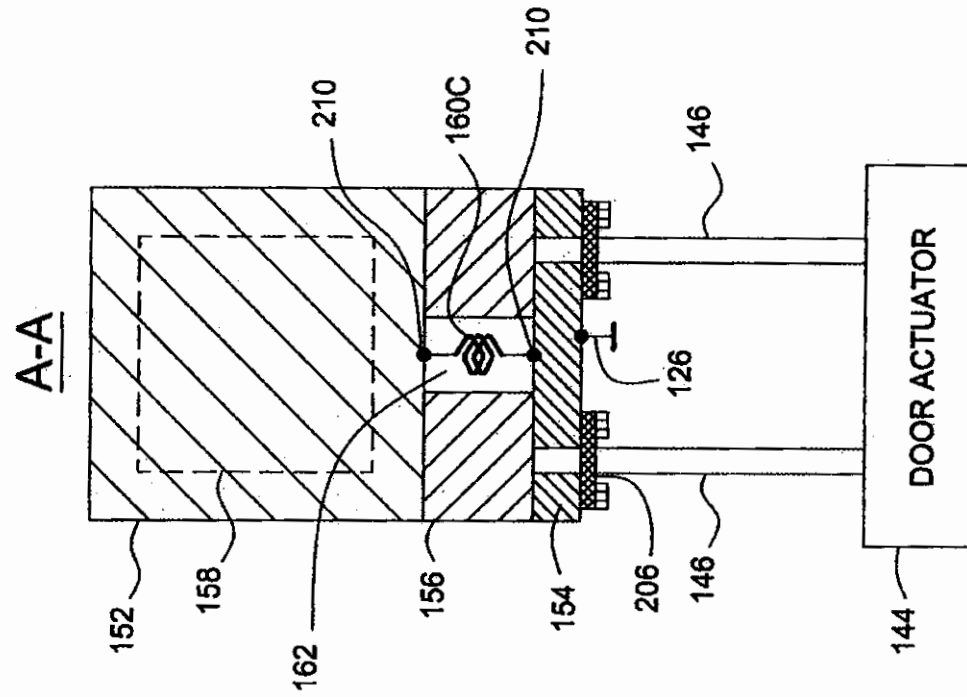


FIG. 2C

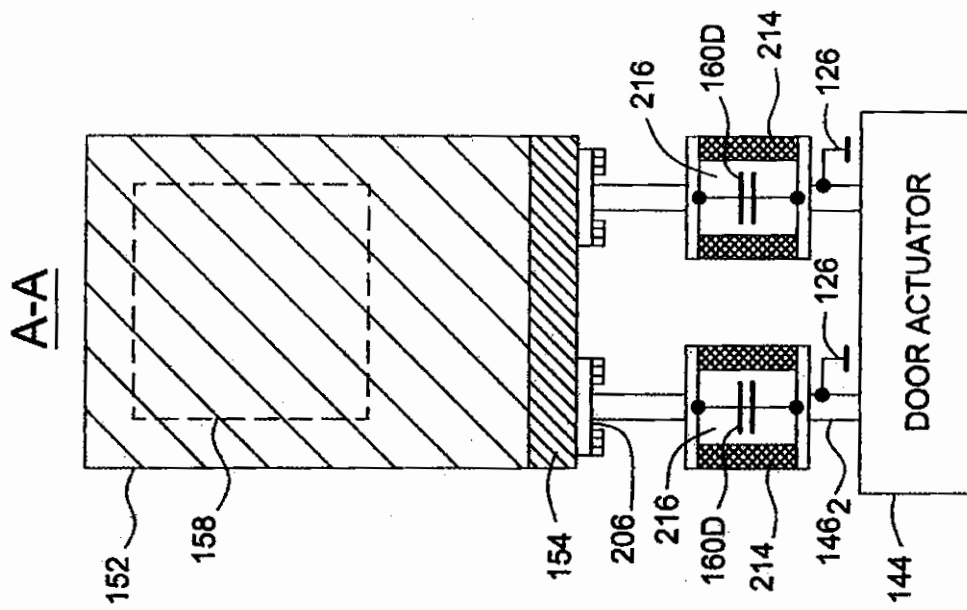


FIG. 2D

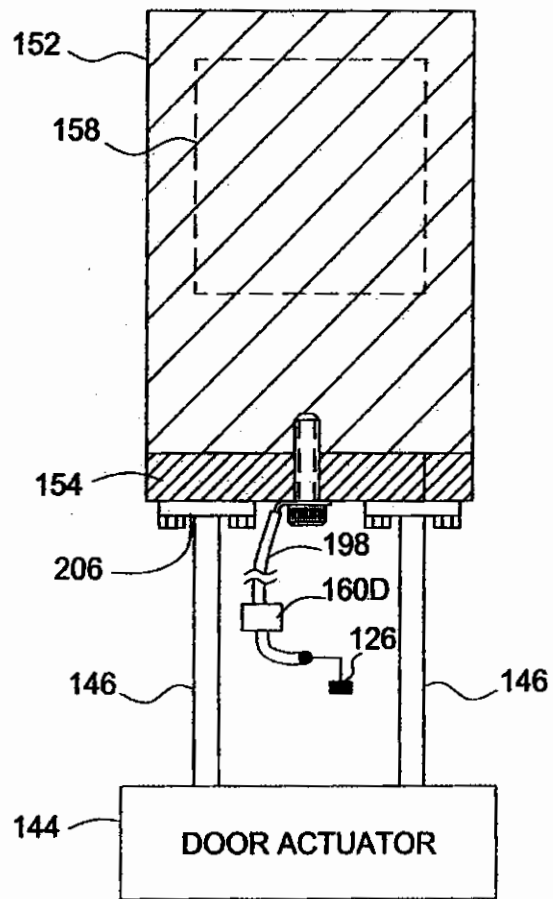
A-A

FIG. 2E

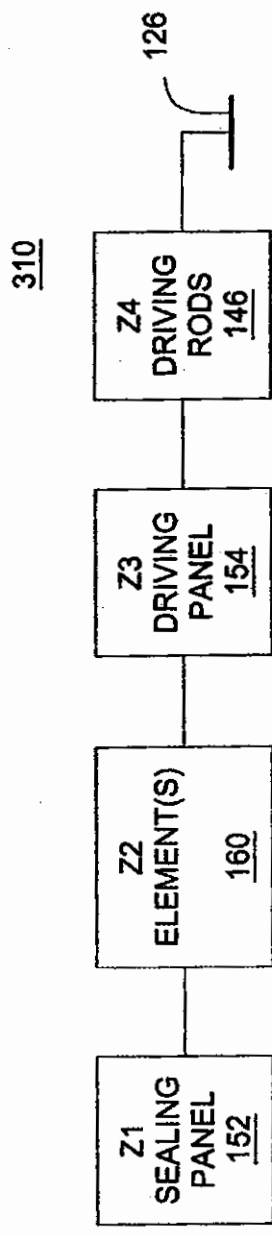


FIG. 3A

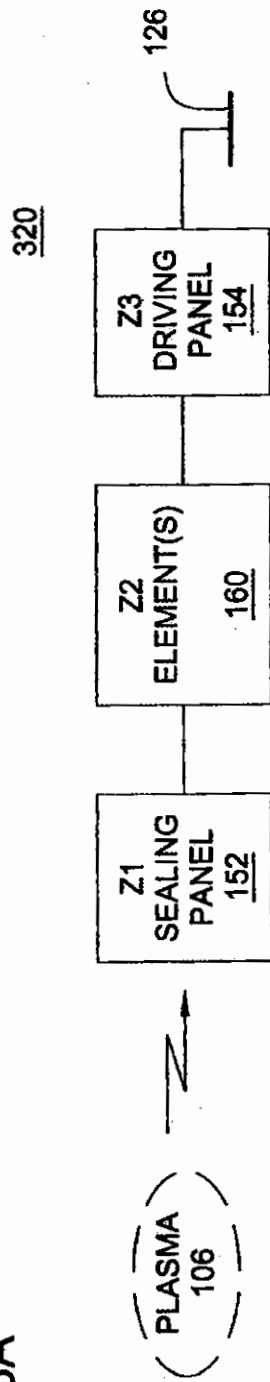


FIG. 3B

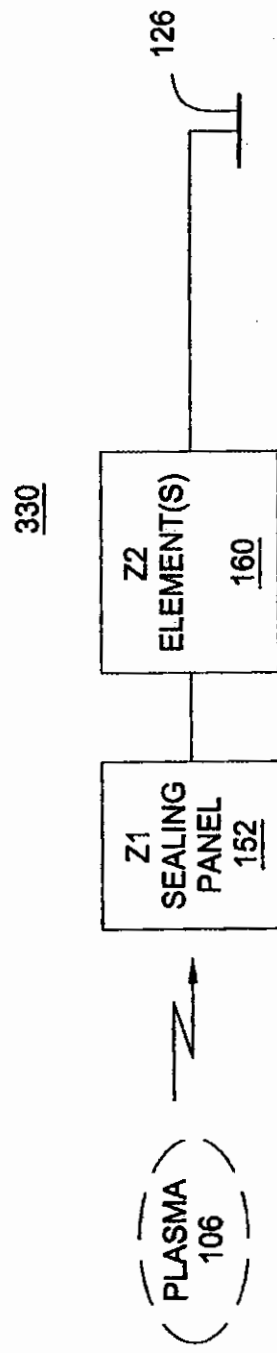


FIG. 3

410

PROVIDING A PLASMA CHAMBER HAVING A SLIT VALVE DOOR  
ADAPTED FOR SELLING A SUBSTRATE TRANSFER PORT OF THE  
PLASMA CHAMBER, THE DOOR BEING ELECTRICALLY COUPLED  
TO GROUND

420

REPLACING AN ELECTRICAL COMPONENT OF A GROUND PATH OF THE  
DOOR USING CONDUCTIVE SHUNTS

430

MEASURING AN IMPEDANCE OF THE DOOR IN THE SEALING POSITION  
TO DETERMINE THE IMPEDANCE, TOGETHER WITH THE OTHER  
COMPONENTS OF THE DOOR GROUND PATH, REQUIRED TO PROVIDE A  
SHORT CIRCUIT PATH AT EXCITATION FREQUENCY OF THE PLASMA

440

REPLACING THE CONDUCTIVE SHUNT WITH A CIRCUIT COMPONENT  
HAVING AN IMPEDANCE VALUE SELECTED SUCH THAT THE DOOR  
GROUND PATH PROVIDES A SHORT CIRCUIT PATH AT EXCITATION  
FREQUENCY OF THE PLASMA

FIG. 4